



IRF9Z14S, SiHF9Z14S, IRF9Z14L, SiHF9Z14L

Vishay Siliconix

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
Http://www.100y.com.tw

Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	- 60	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V	0.50
Q_g (Max.) (nC)	12	
Q_{gs} (nC)	3.8	
Q_{gd} (nC)	5.1	
Configuration	Single	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Advanced Process Technology
- Surface Mount (IRF9Z14S, SiHF9Z14S)
- Low-Profile Through-Hole (IRF9Z14L, SiHF9Z14L)
- 175 °C Operating Temperature
- Fast Switching
- P-Channel
- Fully Avalanche Rated
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT
HALOGEN
FREE
Available

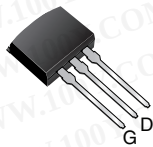
DESCRIPTION

Third generation Power MOSFETs from Vishay utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

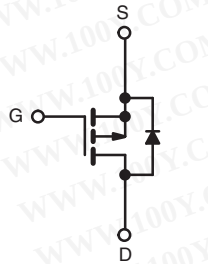
The D²PAK is a surface mount power package capable of accommodating die size up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

The through-hole version (IRF9Z14L, SiHF9Z14L) is available for low-profile applications.

I²PAK (TO-262)



D²PAK (TO-263)



P-Channel MOSFET

ORDERING INFORMATION

Package	D ² PAK (TO-263)	D ² PAK (TO-263)	I ² PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHF9Z14S-GE3	SiHF9Z14STRL-GE3 ^a	SiHF9Z14L-GE3
Lead (Pb)-free	IRF9Z14SPbF	IRF9Z14STRLPbF ^a	IRF9Z14LPbF
	SiHF9Z14S-E3	SiHF9Z14STL-E3 ^a	SiHF9Z14L-E3

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^e	I_D	- 6.7	A
		- 4.7	
Pulsed Drain Current ^{a, e}	I_{DM}	- 27	
Linear Derating Factor		0.29	W/°C
Single Pulse Avalanche Energy ^{b, e}	E_{AS}	140	mJ
Avalanche Current ^a	I_{AR}	- 6.7	A
Repetitive Avalanche Energy ^a	E_{AR}	4.3	mJ
Maximum Power Dissipation	P_D	43	W
		3.7	
Peak Diode Recovery dV/dt ^{c, e}	dV/dt	- 4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = -25$ V, starting $T_J = 25$ °C, $L = 3.6$ mH, $R_g = 25$ Ω , $I_{AS} = -6.7$ A (see fig. 12).
- $I_{SD} \leq -6.7$ A, $dI/dt \leq 90$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.
- Uses IRF9Z14, SiHF9Z14 data and test conditions.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mounted, steady-state) ^a	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.5	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$, $I_D = -250\ \mu\text{A}$	-60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25°C , $I_D = -1\ \text{mA}^c$	-	-0.06	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\ \text{V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\ \text{V}$, $V_{GS} = 0\ \text{V}$	-	-	-100	μA
		$V_{DS} = -48\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 150^\circ\text{C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\ \text{V}$, $I_D = -4.0\ \text{A}^b$	-	-	0.5	Ω
Forward Transconductance	g_{fs}	$V_{DS} = -25\ \text{V}$, $I_D = -4.0\ \text{A}^c$	1.4	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\ \text{V}$, $V_{DS} = -25\ \text{V}$, $f = 1.0\ \text{MHz}$, see fig. 5 ^c	-	270	-	pF
Output Capacitance	C_{oss}		-	170	-	
Reverse Transfer Capacitance	C_{rss}		-	31	-	
Total Gate Charge	Q_g	$V_{GS} = -10\ \text{V}$, $I_D = -6.7\ \text{A}$, $V_{DS} = -48\ \text{V}$, see fig. 6 and 13 ^{b, c}	-	-	12	nC
Gate-Source Charge	Q_{gs}		-	-	3.8	
Gate-Drain Charge	Q_{gd}		-	-	5.1	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\ \text{V}$, $I_D = -6.7\ \text{A}$, $R_g = 24\ \Omega$, $R_D = 4.0\ \Omega$, see fig. 10 ^b	-	11	-	ns
Rise Time	t_r		-	63	-	
Turn-Off Delay Time	$t_{d(off)}$		-	10	-	
Fall Time	t_f		-	31	-	
Internal Source Inductance	L_S	Between lead, and center of die contact	-	7.5	-	nH
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	-6.7	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	-27	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}$, $I_S = -6.7\ \text{A}$, $V_{GS} = 0\ \text{V}^b$	-	-	-5.5	V
Drain-Source Body Diode Characteristics						
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}$, $I_F = -6.7\ \text{A}$, $dI/dt = 100\ \text{A}/\mu\text{s}^b, c$	-	80	160	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	96	190	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\ \mu\text{s}$; duty cycle $\leq 2\ \%$.
- Uses IRF9Z14, SiHF9Z14 data and test conditions.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

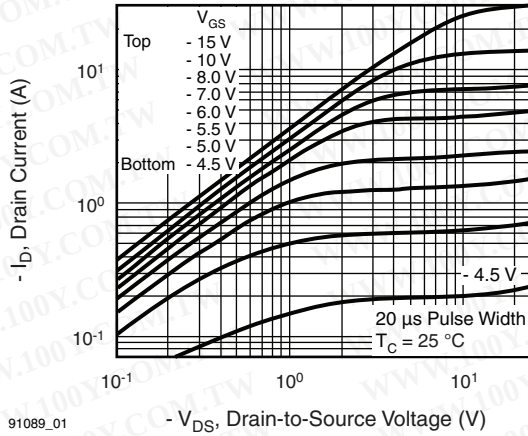


Fig. 1 - Typical Output Characteristics

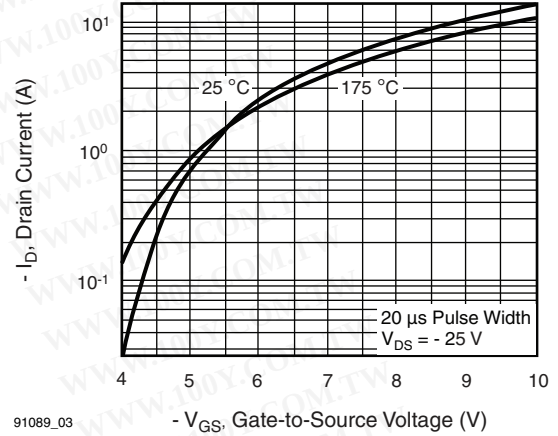


Fig. 3 - Typical Transfer Characteristics

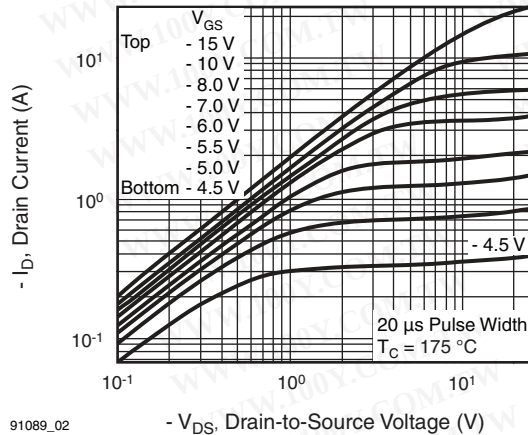


Fig. 2 - Typical Output Characteristics

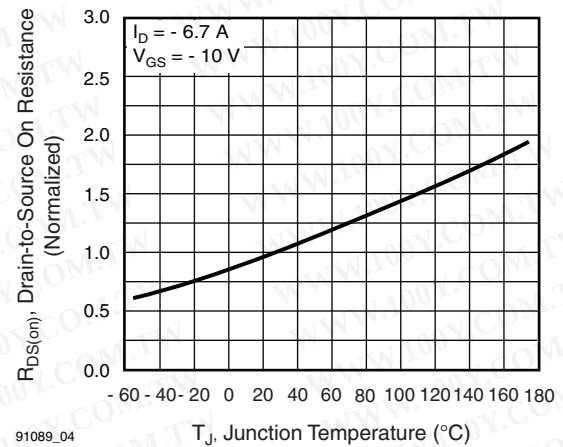


Fig. 4 - Normalized On-Resistance vs. Temperature

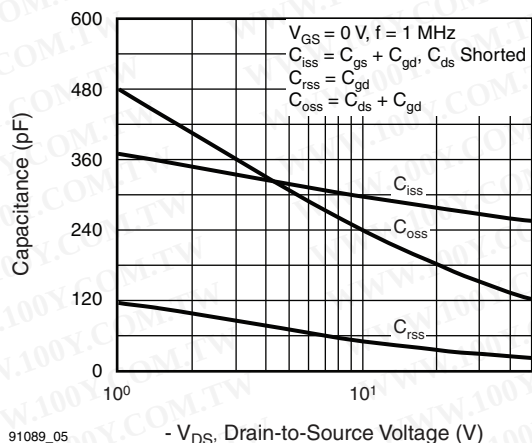


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

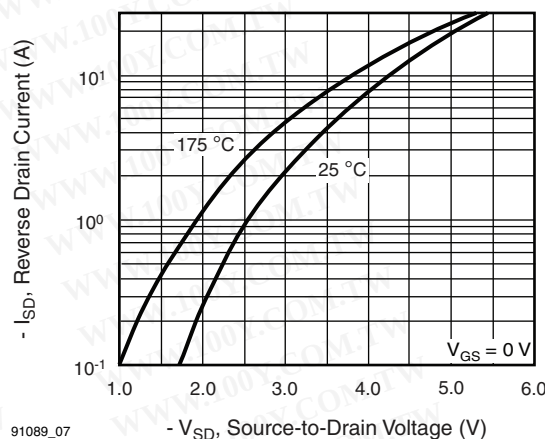


Fig. 7 - Typical Source-Drain Diode Forward Voltage

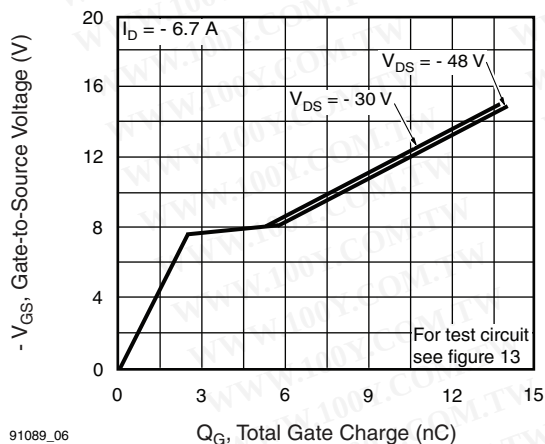


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

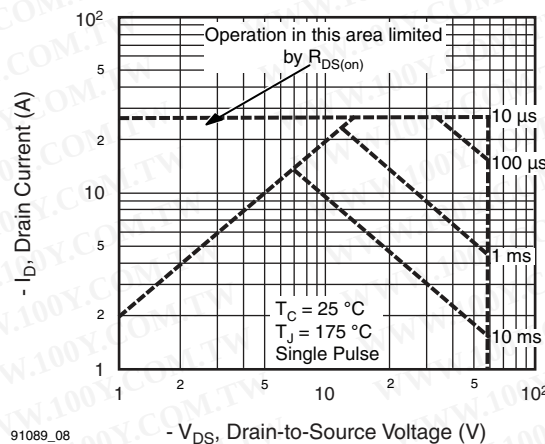


Fig. 8 - Maximum Safe Operating Area

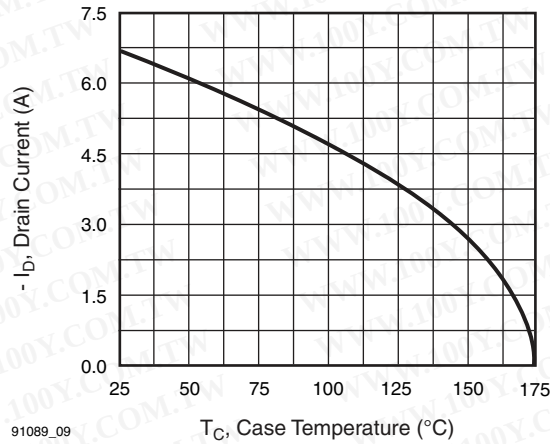


Fig. 9 - Maximum Drain Current vs. Case Temperature

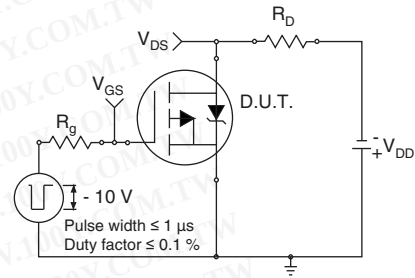


Fig. 10a - Switching Time Test Circuit

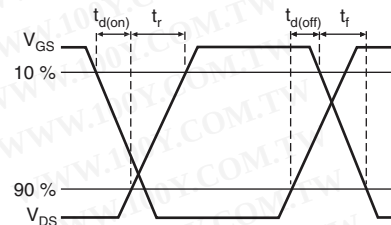


Fig. 10b - Switching Time Waveforms

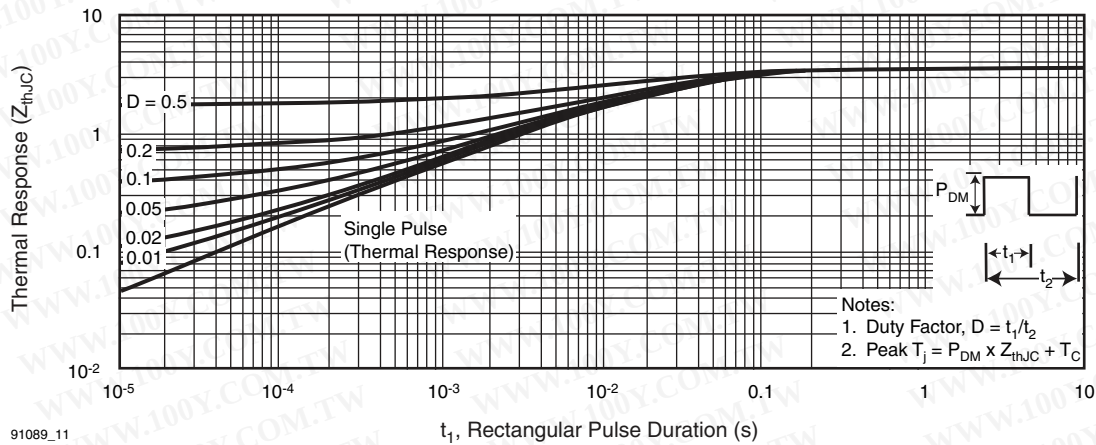


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

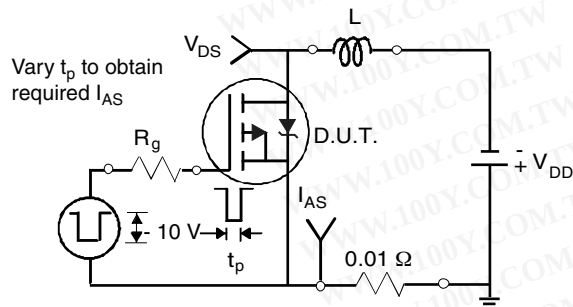


Fig. 12a - Unclamped Inductive Test Circuit

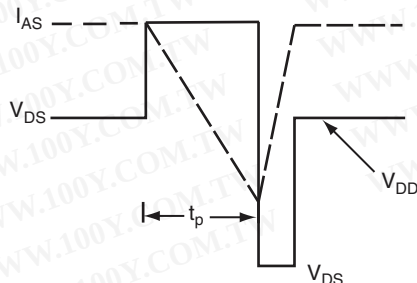


Fig. 12b - Unclamped Inductive Waveforms

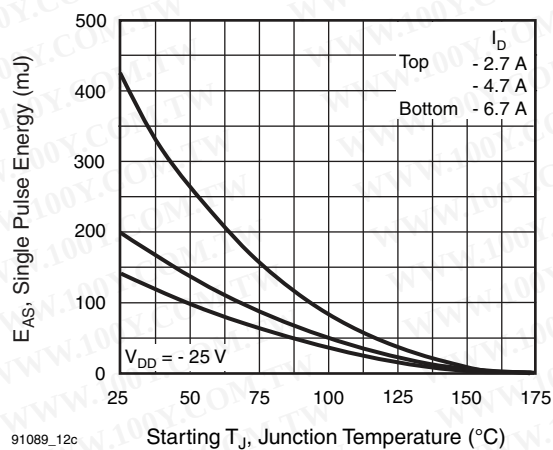


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

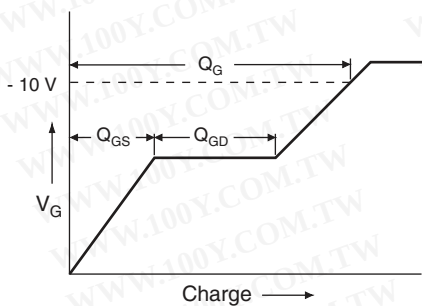


Fig. 13a - Basic Gate Charge Waveform

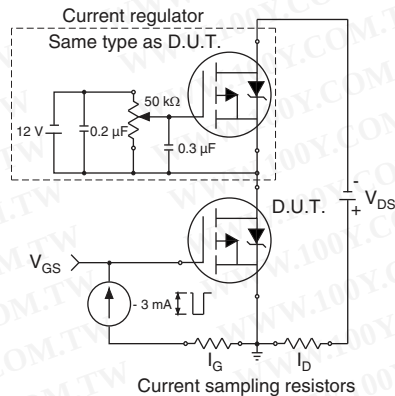
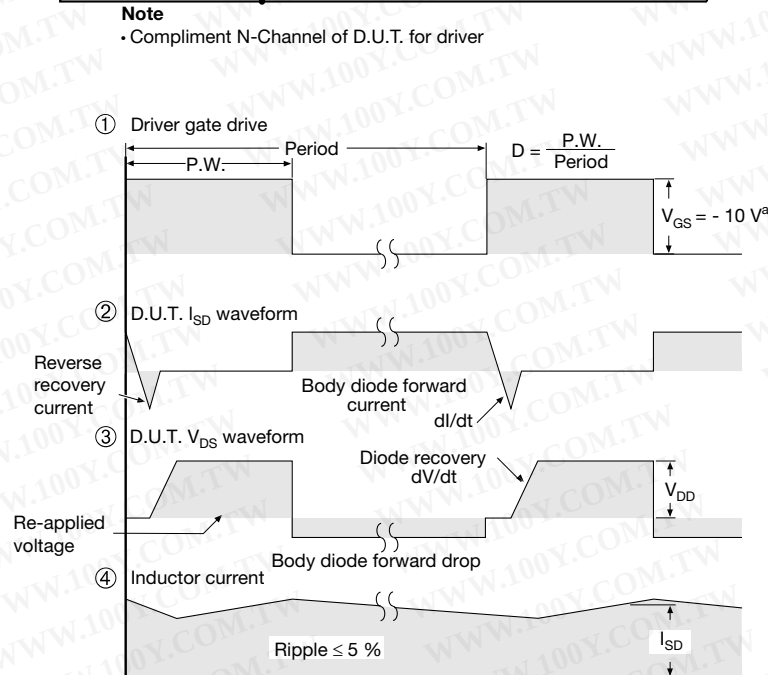
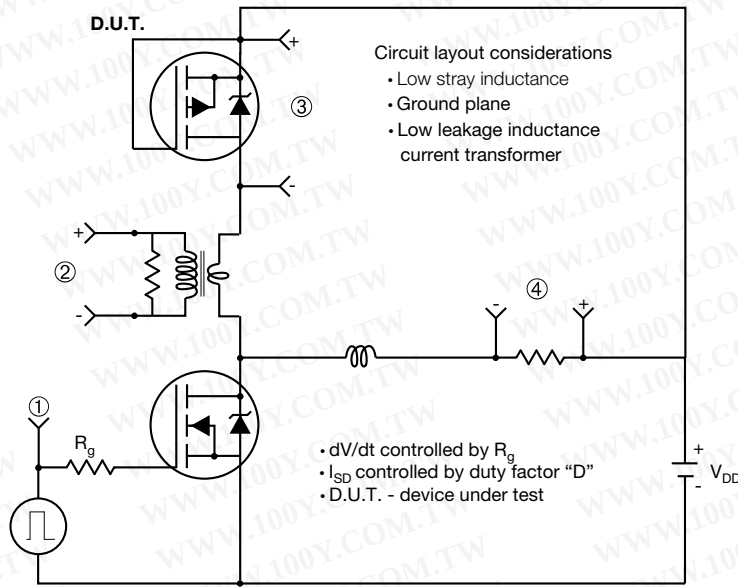


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



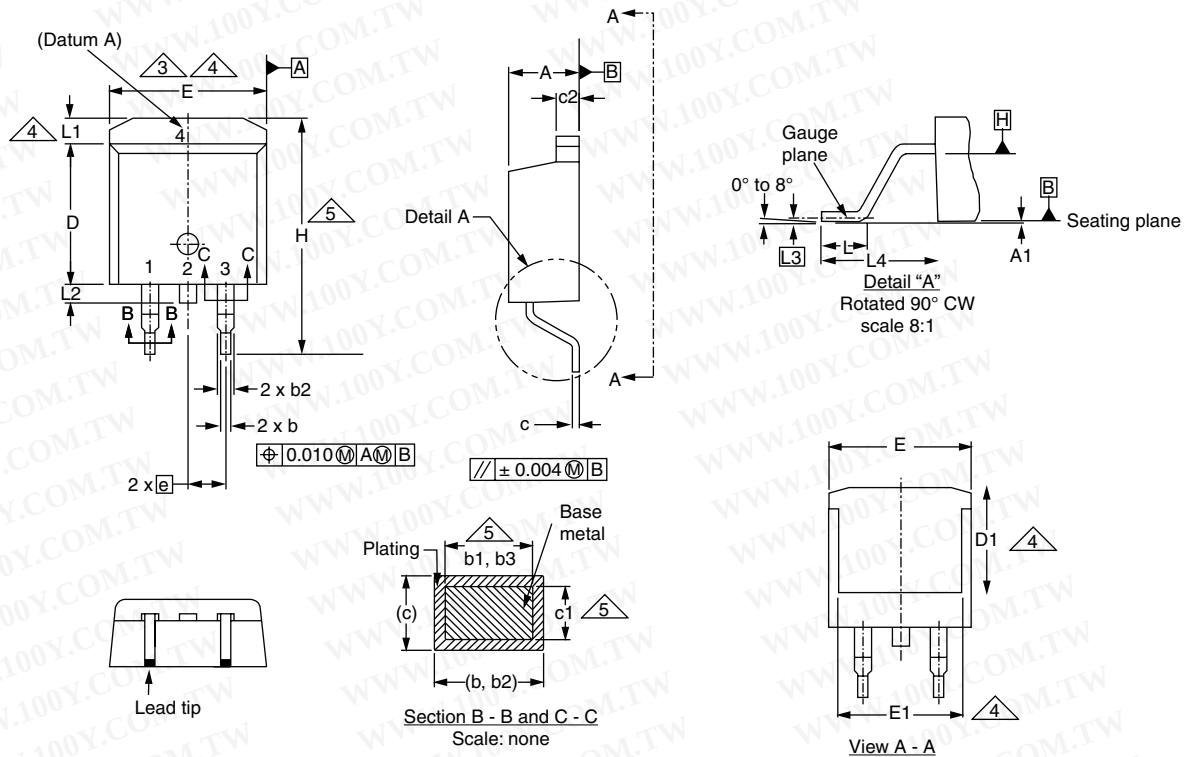
Note
a. $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 14 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91089.



TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.



勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.